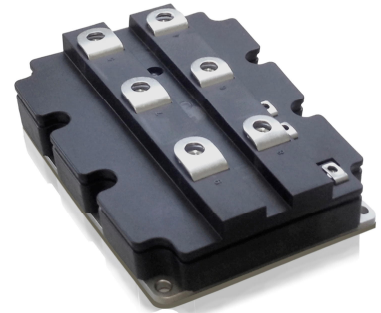


5SNA 3600E170300

HiPak IGBT Module

 $V_{CE} = 1700 \text{ V}$
 $I_C = 3600 \text{ A}$

Ultra low-loss, rugged SPT+ chip-set
 Smooth switching SPT+ chip-set for good EMC
 AlSiC base-plate for high power cycling capability
 AlN substrate for low thermal resistance
 Improved high reliability package
 Recognized under UL1557, File E196689



Maximum rated values ¹⁾

Parameter	Symbol	Conditions	min	max	Unit
Collector-emitter voltage	V_{CES}	$V_{GE} = 0 \text{ V}$, $T_{vj} \geq 25 \text{ }^{\circ}\text{C}$		1700	V
DC collector current	I_C	$T_C = 70 \text{ }^{\circ}\text{C}$, $T_{vj} = 150 \text{ }^{\circ}\text{C}$		3600	A
Peak collector current	I_{CM}	$t_p = 1 \text{ ms}$		7200	A
Gate-emitter voltage	V_{GES}		-20	20	V
Total power dissipation	P_{tot}	$T_C = 25 \text{ }^{\circ}\text{C}$, $T_{vj} = 150 \text{ }^{\circ}\text{C}$		17800	W
DC forward current	I_F			3600	A
Peak forward current	I_{FRM}	$t_p = 1 \text{ ms}$		7200	A
Surge current	I_{FSM}	$V_R = 0 \text{ V}$, $T_{vj} = 150 \text{ }^{\circ}\text{C}$, $t_p = 10 \text{ ms}$, half-sinewave		18000	A
IGBT short circuit SOA	t_{psc}	$V_{CC} = 1200 \text{ V}$, $V_{CEM \text{ CHIP}} \leq 1700 \text{ V}$ $V_{GE} \leq 15 \text{ V}$, $T_{vj} \leq 150 \text{ }^{\circ}\text{C}$		10	μs
Isolation voltage	V_{isol}	1 min, $f = 50 \text{ Hz}$		4000	V
Junction temperature	T_{vj}			175	$^{\circ}\text{C}$
Junction operating temperature	$T_{vj(op)}$		-50	150	$^{\circ}\text{C}$
Case temperature	T_C		-50	150	$^{\circ}\text{C}$
Storage temperature	T_{stg}		-50	125	$^{\circ}\text{C}$
Mounting torques ²⁾	M_s	Base-heatsink, M6 screws	4	6	Nm
	M_{t1}	Main terminals, M8 screws	8	10	
	M_{t2}	Auxiliary terminals, M4 screws	2	3	

¹⁾ Maximum rated values indicate limits beyond which damage to the device may occur per IEC 60747

²⁾ For detailed mounting instructions refer to Document No. 5SYA 2039

IGBT characteristic values ³⁾

Parameter	Symbol	Conditions	min	typ	max	Unit	
Collector (-emitter) breakdown voltage	$V_{(BR)CES}$	$V_{GE} = 0 \text{ V}$, $I_C = 10 \text{ mA}$, $T_{vj} = 25 \text{ }^{\circ}\text{C}$	1700			V	
Collector-emitter ⁴⁾ saturation voltage	$V_{CE \text{ sat}}$	$I_C = 3600 \text{ A}$, $V_{GE} = 15 \text{ V}$	$T_{vj} = 25 \text{ }^{\circ}\text{C}$	2.2	2.5	2.8	V
			$T_{vj} = 125 \text{ }^{\circ}\text{C}$	2.7	3.0	3.3	V
			$T_{vj} = 150 \text{ }^{\circ}\text{C}$		3.1		V
Collector cut-off current	I_{CES}	$V_{CE} = 1700 \text{ V}$, $V_{GE} = 0 \text{ V}$	$T_{vj} = 25 \text{ }^{\circ}\text{C}$		0.04	1	mA
			$T_{vj} = 125 \text{ }^{\circ}\text{C}$		30	60	mA
			$T_{vj} = 150 \text{ }^{\circ}\text{C}$		170		mA
Gate leakage current	I_{GES}	$V_{CE} = 0 \text{ V}$, $V_{GE} = \pm 20 \text{ V}$, $T_{vj} = 125 \text{ }^{\circ}\text{C}$	-500		500	nA	
Gate-emitter threshold voltage	$V_{GE(TO)}$	$I_C = 240 \text{ mA}$, $V_{CE} = V_{GE}$, $T_{vj} = 25 \text{ }^{\circ}\text{C}$	5.3		7.3	V	
Gate charge	Q_{ge}	$I_C = 3600 \text{ A}$, $V_{CE} = 900 \text{ V}$, $V_{GE} = -15 \text{ V} \dots 15 \text{ V}$		21		μC	
Input capacitance	C_{ies}	$V_{CE} = 25 \text{ V}$, $V_{GE} = 0 \text{ V}$, $f = 1 \text{ MHz}$, $T_{vj} = 25 \text{ }^{\circ}\text{C}$		239		nF	
Output capacitance	C_{oes}			20.9		nF	
Reverse transfer capacitance	C_{res}			9.24		nF	
Turn-on delay time	$t_{d(on)}$	$V_{CC} = 900 \text{ V}$, $I_C = 3600 \text{ A}$, $R_G = 0.6 \text{ }\Omega$, $C_{GE} = 0 \text{ nF}$, $V_{GE} = \pm 15 \text{ V}$, $L_{\sigma} = 50 \text{ nH}$, inductive load	$T_{vj} = 25 \text{ }^{\circ}\text{C}$		480		ns
			$T_{vj} = 125 \text{ }^{\circ}\text{C}$		510		ns
			$T_{vj} = 150 \text{ }^{\circ}\text{C}$		520		ns
Rise time	t_r		$T_{vj} = 25 \text{ }^{\circ}\text{C}$		290		ns
			$T_{vj} = 125 \text{ }^{\circ}\text{C}$		310		ns
			$T_{vj} = 150 \text{ }^{\circ}\text{C}$		315		ns
Turn-off delay time	$t_{d(off)}$	$V_{CC} = 900 \text{ V}$, $I_C = 3600 \text{ A}$, $R_G = 0.6 \text{ }\Omega$, $C_{GE} = 0 \text{ nF}$, $V_{GE} = \pm 15 \text{ V}$, $L_{\sigma} = 50 \text{ nH}$, inductive load	$T_{vj} = 25 \text{ }^{\circ}\text{C}$		1160		ns
			$T_{vj} = 125 \text{ }^{\circ}\text{C}$		1260		ns
			$T_{vj} = 150 \text{ }^{\circ}\text{C}$		1290		ns
Fall time	t_f		$T_{vj} = 25 \text{ }^{\circ}\text{C}$		270		ns
			$T_{vj} = 125 \text{ }^{\circ}\text{C}$		300		ns
			$T_{vj} = 150 \text{ }^{\circ}\text{C}$		310		ns
Turn-on switching energy	E_{on}	$V_{CC} = 900 \text{ V}$, $I_C = 3600 \text{ A}$, $R_G = 0.6 \text{ }\Omega$, $C_{GE} = 0 \text{ nF}$, $V_{GE} = \pm 15 \text{ V}$, $L_{\sigma} = 50 \text{ nH}$, inductive load	$T_{vj} = 25 \text{ }^{\circ}\text{C}$		800		mJ
			$T_{vj} = 125 \text{ }^{\circ}\text{C}$		1100		mJ
			$T_{vj} = 150 \text{ }^{\circ}\text{C}$		1200		mJ
Turn-off switching energy	E_{off}	$V_{CC} = 900 \text{ V}$, $I_C = 3600 \text{ A}$, $R_G = 0.6 \text{ }\Omega$, $C_{GE} = 0 \text{ nF}$, $V_{GE} = \pm 15 \text{ V}$, $L_{\sigma} = 50 \text{ nH}$, inductive load	$T_{vj} = 25 \text{ }^{\circ}\text{C}$		1330		mJ
			$T_{vj} = 125 \text{ }^{\circ}\text{C}$		1600		mJ
			$T_{vj} = 150 \text{ }^{\circ}\text{C}$		1690		mJ
Short circuit current	I_{SC}	$t_{psc} \leq 10 \text{ }\mu\text{s}$, $V_{GE} = 15 \text{ V}$, $V_{CC} = 1200 \text{ V}$, $V_{CEM \text{ CHIP}} \leq 1700 \text{ V}$	$T_{vj} = 150 \text{ }^{\circ}\text{C}$	10000		A	

³⁾ Characteristic values according to IEC 60747 – 9

⁴⁾ Collector-emitter saturation voltage is given at chip level

Diode characteristic values ⁵⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
Forward voltage ⁶⁾	V _F	I _F = 3600 A	T _{vj} = 25 °C	1.85	2.2	V
			T _{vj} = 125 °C	1.95	2.3	V
			T _{vj} = 150 °C	1.9		V
Reverse recovery current	I _{rr}	V _{CC} = 900 V, I _F = 3600 A, V _{GE} = ±15 V, R _G = 0.6 Ω, C _{GE} = 0 nF, di/dt = 11.5 kA/μs L _σ = 50 nH, inductive load	T _{vj} = 25 °C	2030		A
			T _{vj} = 125 °C	2340		A
			T _{vj} = 150 °C	2500		A
Recovered charge	Q _{rr}		T _{vj} = 25 °C	1000		μC
			T _{vj} = 125 °C	1560		μC
			T _{vj} = 150 °C	1820		μC
Reverse recovery time	t _{rr}		T _{vj} = 25 °C	900		ns
			T _{vj} = 125 °C	1230		ns
			T _{vj} = 150 °C	1320		ns
Reverse recovery energy	E _{rec}		T _{vj} = 25 °C	710		mJ
			T _{vj} = 125 °C	1080		mJ
			T _{vj} = 150 °C	1260		mJ

⁵⁾ Characteristic values according to IEC 60747 – 2

⁶⁾ Forward voltage is given at chip level

Package properties ⁷⁾

Parameter	Symbol	Conditions	min	typ	max	Unit
IGBT thermal resistance junction to case	$R_{th(j-c)IGBT}$				0.007	K/W
Diode thermal resistance junction to case	$R_{th(j-c)DIODE}$				0.012	K/W
IGBT thermal resistance ²⁾ case to heatsink	$R_{th(c-s)IGBT}$	IGBT per switch, λ grease = 1W/m x K		0.009		K/W
Diode thermal resistance ²⁾ case to heatsink	$R_{th(c-s)DIODE}$	Diode per switch, λ grease = 1W/m x K		0.018		K/W
Comparative tracking index	CTI		600			
Module stray inductance	$L_{\sigma CE}$			8		nH
Resistance, terminal-chip	$R_{CC'+EE'}$	$T_C = 25\text{ °C}$		0.055		m Ω
		$T_C = 125\text{ °C}$		0.075		
		$T_C = 150\text{ °C}$		0.080		

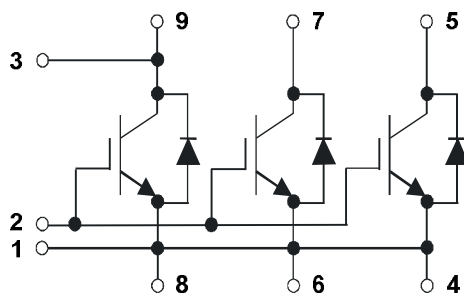
²⁾ For detailed mounting instructions refer to ABB Document No. 5SYA 2039

Mechanical properties ⁷⁾

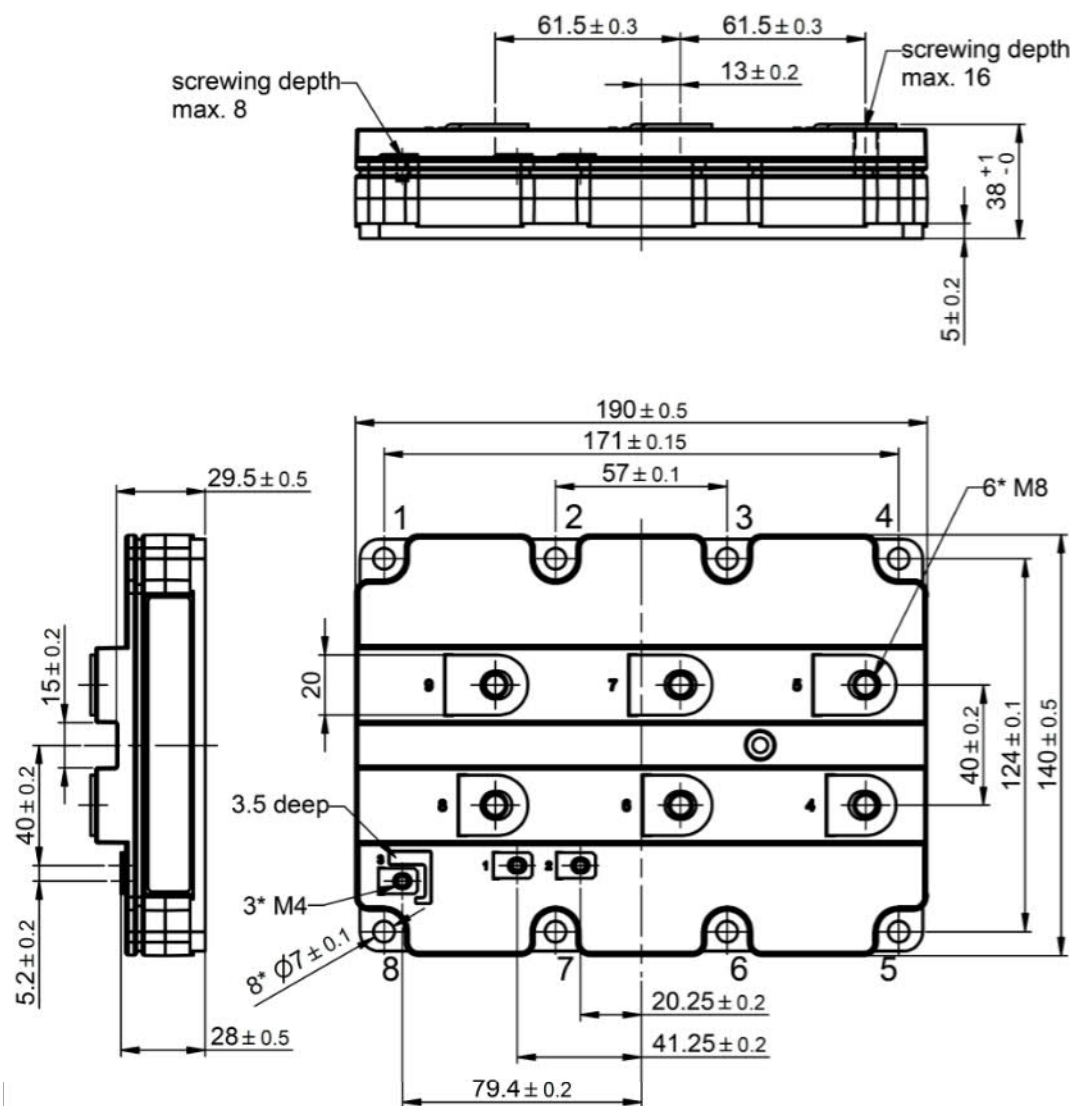
Parameter	Symbol	Conditions	min	typ	max	Unit
Dimensions	L x W x H	Typical	190 x 140 x 38			mm
Clearance distance in air	d_a	according to IEC 60664-1 and EN 50124-1	Term. to base:	23		mm
			Term. to term:	19		
Surface creepage distance	d_s	according to IEC 60664-1 and EN 50124-1	Term. to base:	28.2		mm
			Term. to term:	28.2		
Mass	m			1210		g

⁷⁾ Package and mechanical properties according to IEC 60747 – 15

Electrical configuration



Outline drawing ²⁾



Note: all dimensions are shown in millimeters

²⁾ For detailed mounting instructions refer to Document No. 5SYA 2039

This is an electrostatic sensitive device, please observe the international standard IEC 60747-1, chap. IX.
This product has been designed and qualified for Industrial Level.

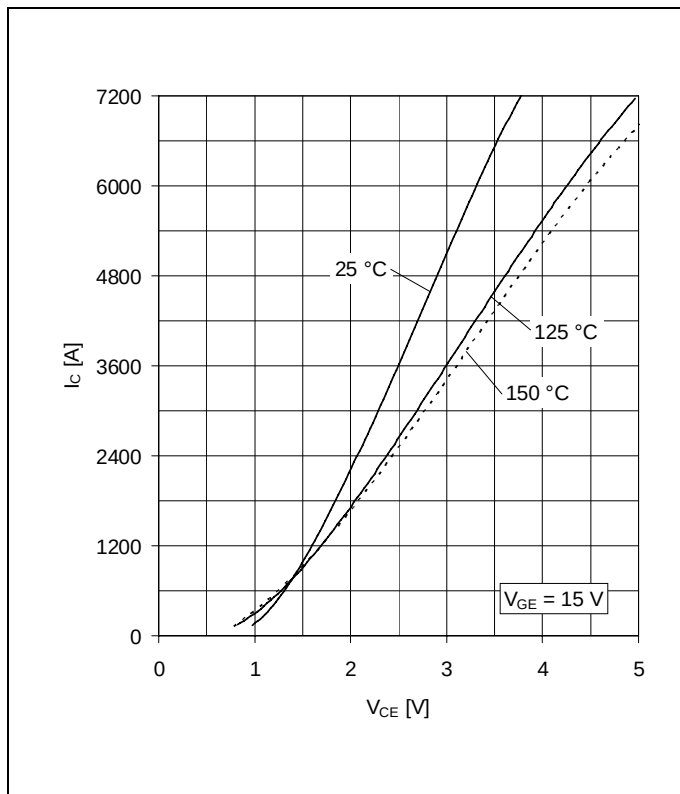


Fig. 1 Typical on-state characteristics, chip level

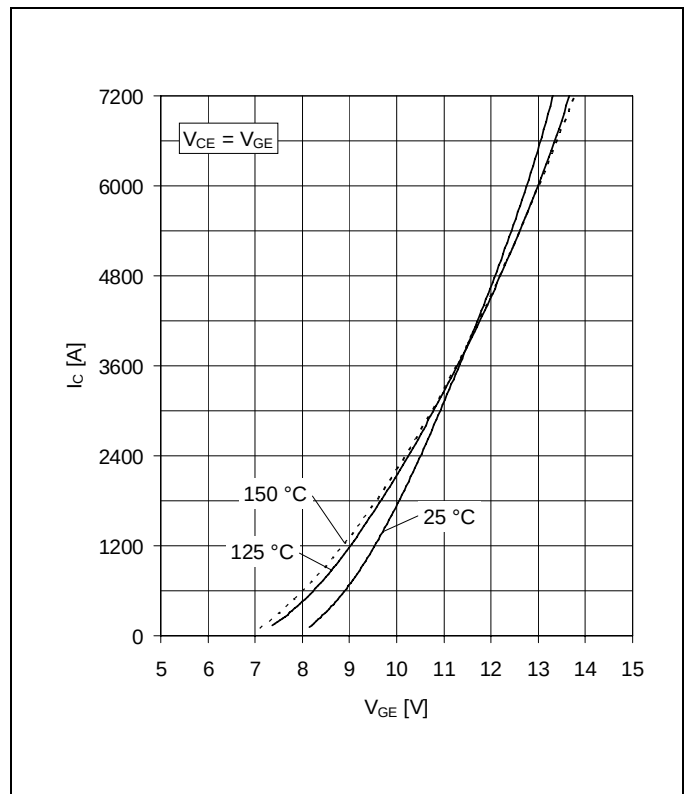


Fig. 2 Typical transfer characteristics, chip level

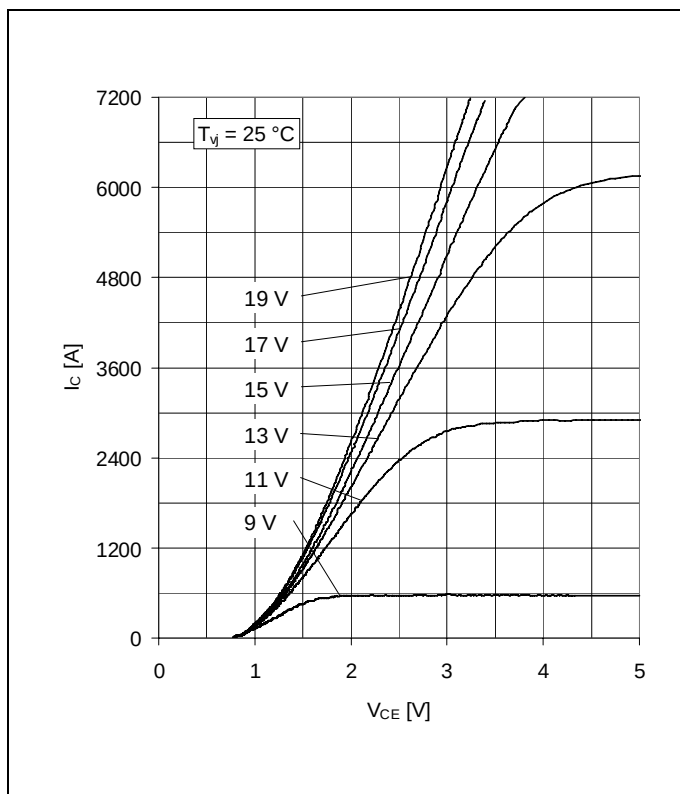


Fig. 3 Typical output characteristics, chip level

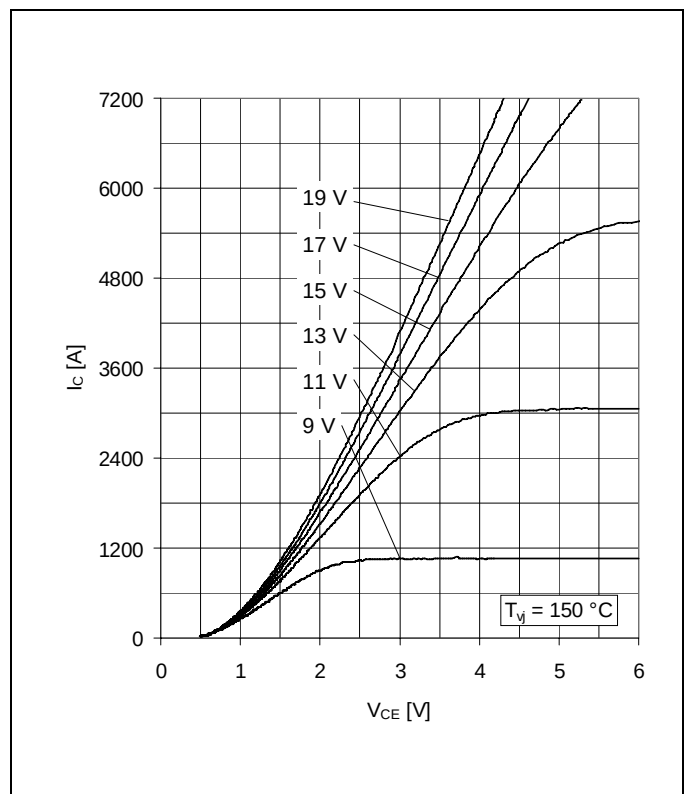


Fig. 4 Typical output characteristics, chip level

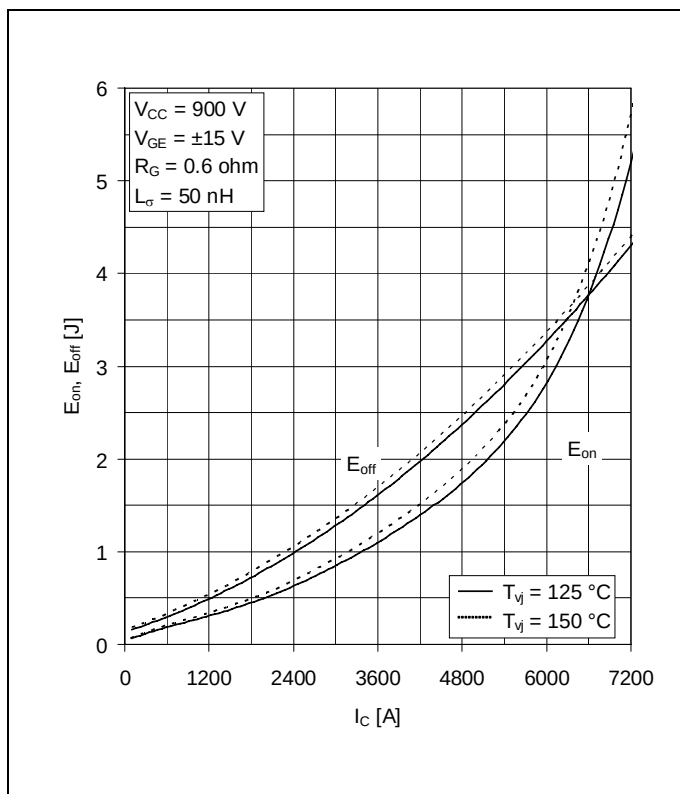


Fig. 5 Typical switching energies per pulse vs. collector current

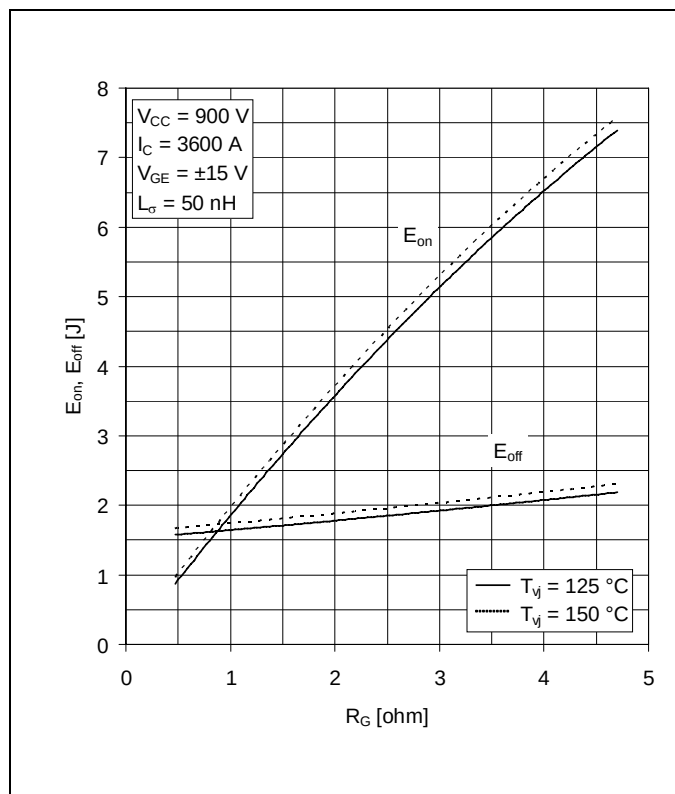


Fig. 6 Typical switching energies per pulse vs. gate resistor

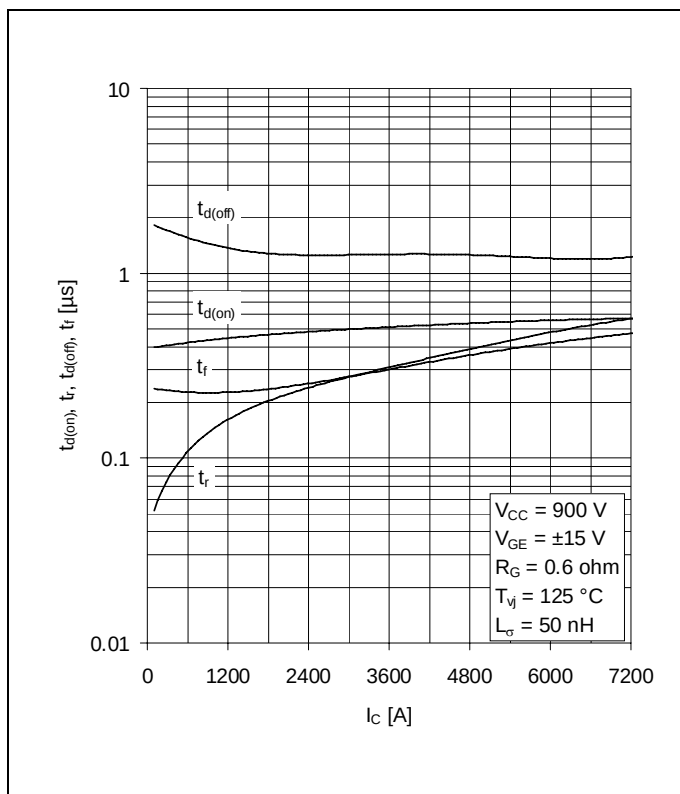


Fig. 7 Typical switching times vs. collector current

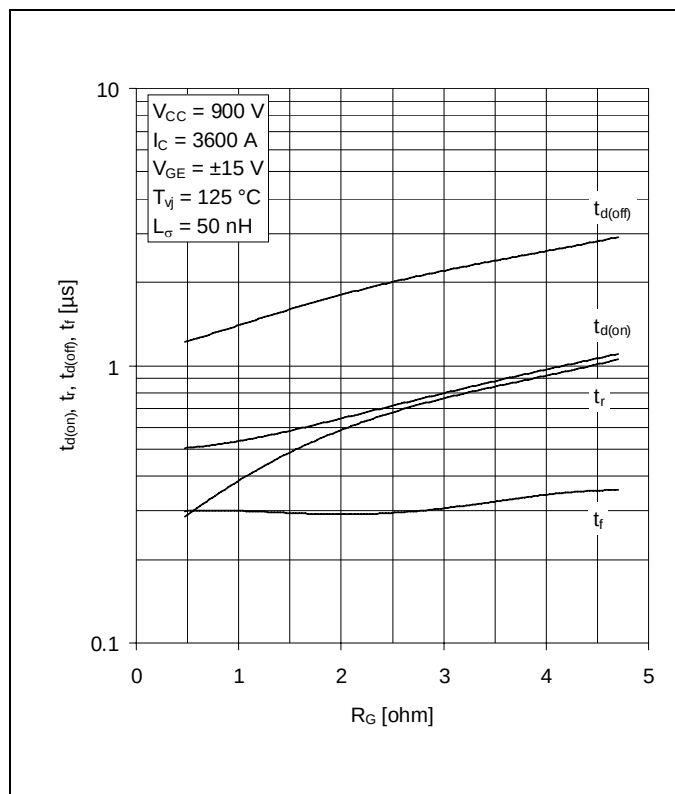


Fig. 8 Typical switching times vs. gate resistor

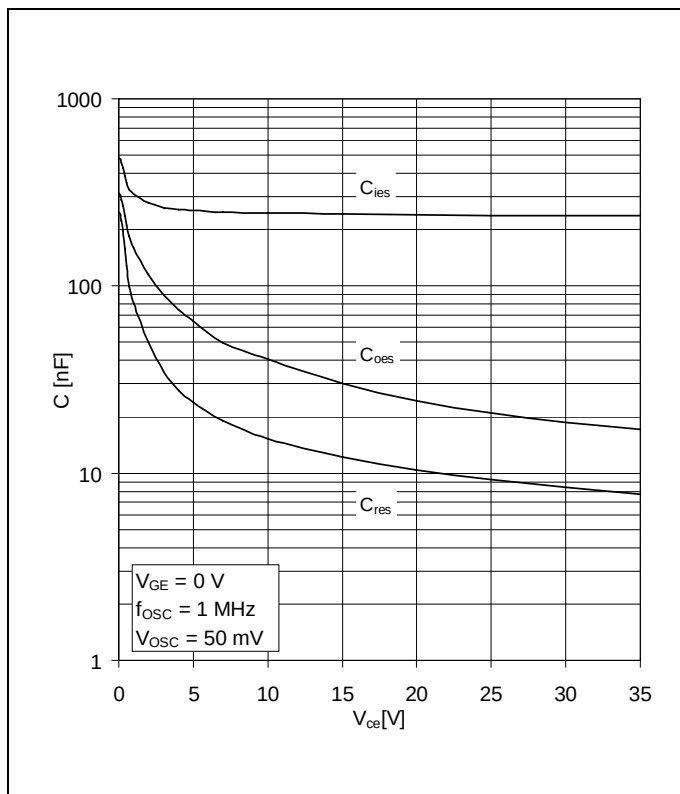


Fig. 9 Typical capacitances vs. collector-emitter voltage

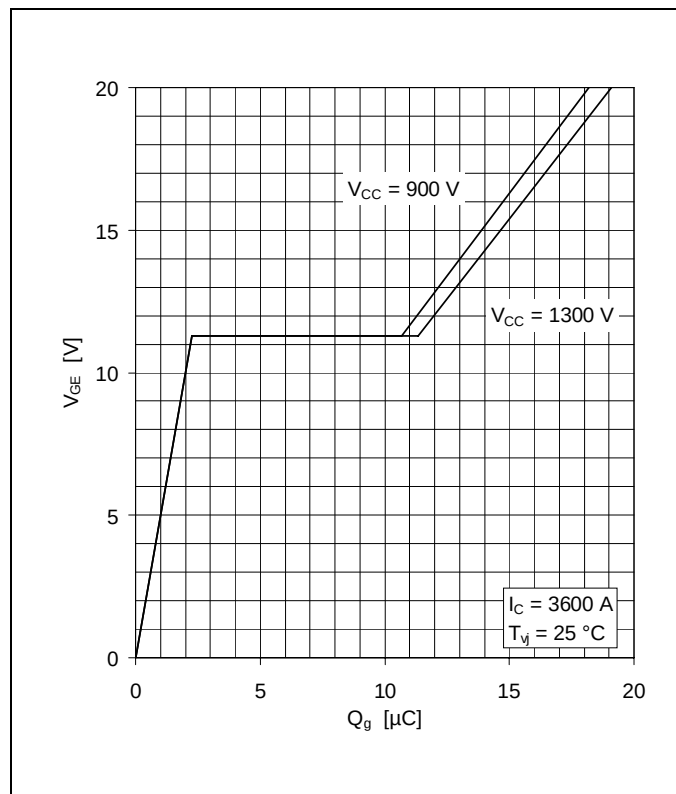


Fig. 10 Typical gate charge characteristics

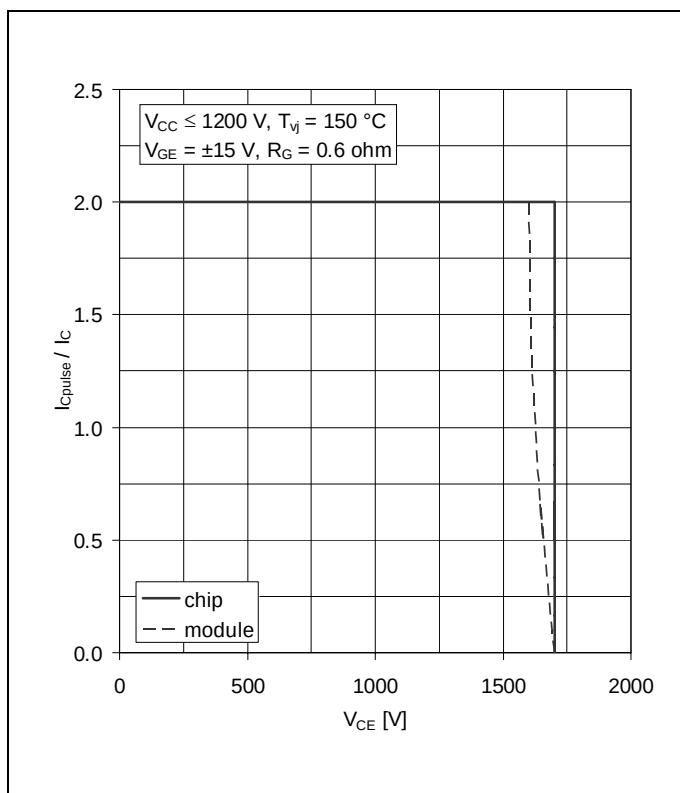


Fig. 11 Turn-off safe operating area (RBSOA)

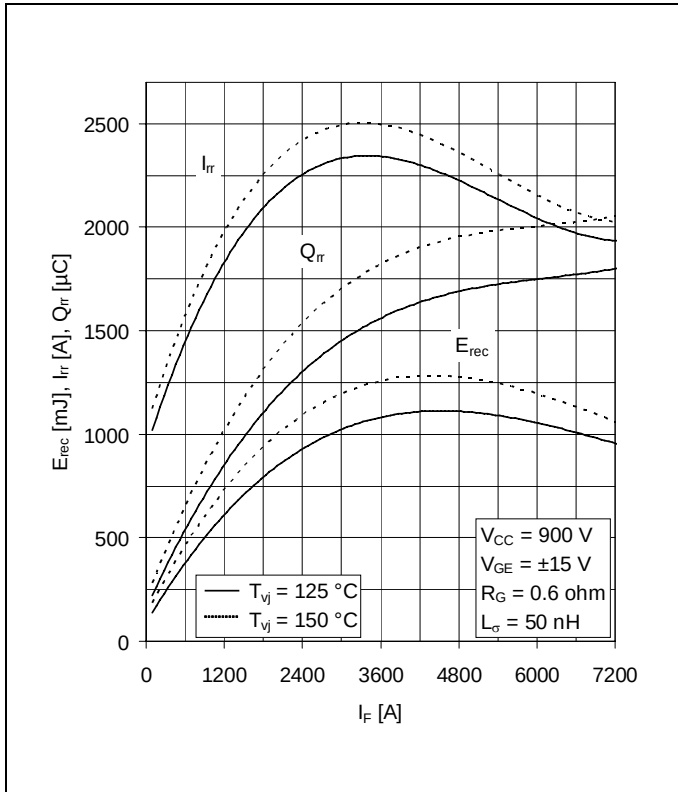


Fig. 12 Typical reverse recovery characteristics vs. forward current

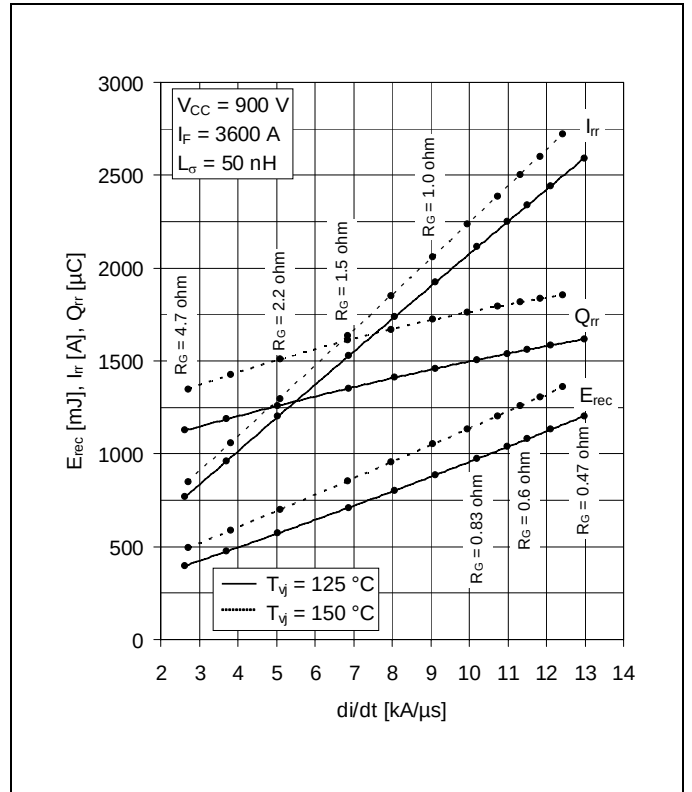


Fig. 13 Typical reverse recovery characteristics vs. di/dt

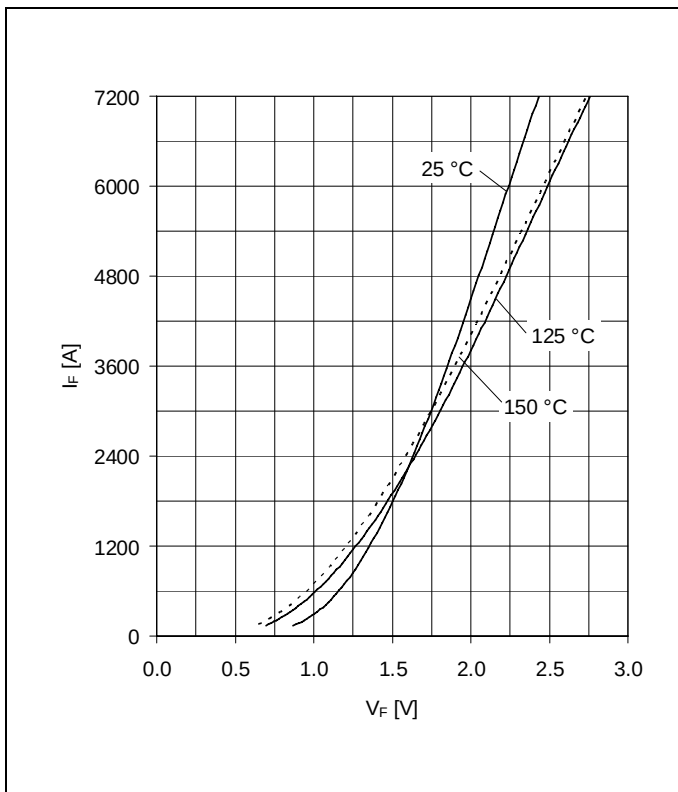


Fig. 14 Typical diode forward characteristics chip level

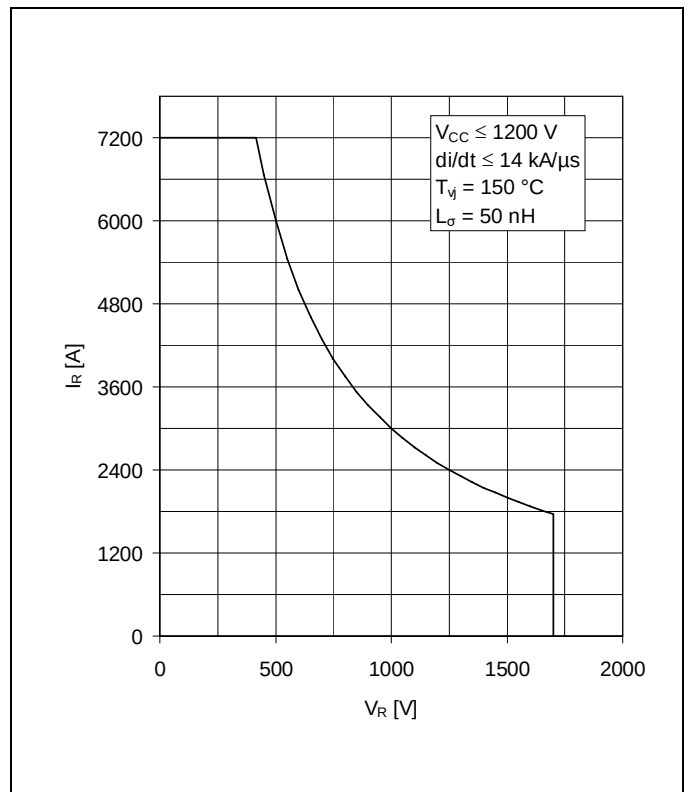


Fig. 15 Safe operating area diode (SOA)

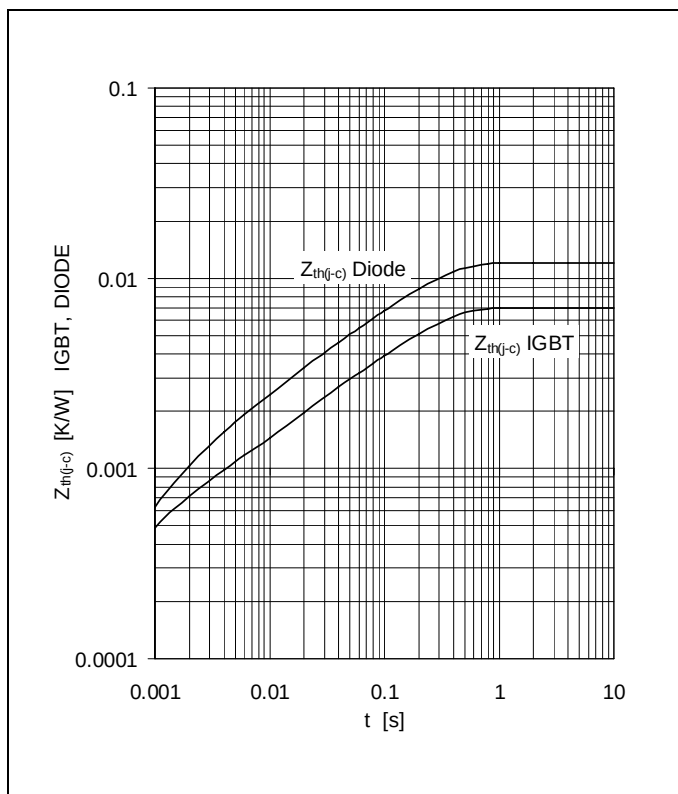


Fig. 16 Thermal impedance vs. time

Analytical function for transient thermal impedance:

$$Z_{th(j-c)}(t) = \sum_{i=1}^n R_i (1 - e^{-t/\tau_i})$$

	i	1	2	3	4	5
IGBT	Ri(K/kW)	5.059	1.201	0.495	0.246	
	τ_i (ms)	202.9	20.3	2.01	0.52	
DIODE	Ri(K/kW)	8.432	1.928	0.866	0.839	
	τ_i (ms)	210	29.6	7.01	1.49	

Related documents:

5SYA 2042 Failure rates of HiPak modules due to cosmic rays
 5SYA 2043 Load – cycle capability of HiPaks
 5SYA 2045 Thermal runaway during blocking
 5SYA 2053 Applying IGBT
 5SYA 2058 Surge currents for IGBT diodes
 5SYA 2093 Thermal design of IGBT modules
 5SYA 2098 Paralleling of IGBT modules
 5SZK 9111 Specification of environmental class for HiPak Storage
 5SZK 9112 Specification of environmental class for HiPak Transportation
 5SZK 9113 Specification of environmental class for HiPak Operation (Industry)
 5SZK 9120 Specification of environmental class for HiPak

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